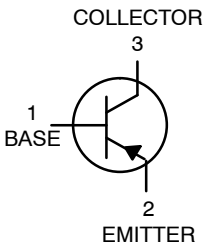
High Voltage Transistor

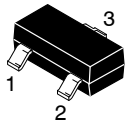
PNP Silicon

BSS63LT1G, NSVBSS63LT1G



Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant



SOT−23
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−100	Vdc
Collector − Emitter Voltage R_{BE} = 10 kΩ	V_{CER}	−110	Vdc
Collector Current − Continuous	I_C	−100	mAdc

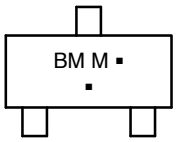
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MARKING DIAGRAM



BM = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BSS63LT1G	SOT−23 (Pb−free)	3000 / Tape & Reel
NSVBSS63LT1G	SOT−23 (Pb−free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I_C = −100 μAdc)	$V_{(BR)CEO}$	−100	–	–	Vdc
Collector – Emitter Breakdown Voltage (I_C = −10 μAdc, I_E = 0, R_{BE} = 10 kΩ)	$V_{(BR)CER}$	−110	–	–	Vdc
Collector – Base Breakdown Voltage (I_E = −10 μAdc, I_E = 0)	$V_{(BR)CBO}$	−110	–	–	Vdc
Emitter – Base Breakdown Voltage (I_E = −10 μAdc)	$V_{(BR)EBO}$	−6.0	–	–	Vdc
Collector Cutoff Current (V_{CB} = −90 Vdc, I_E = 0)	I_{CBO}	–	–	−100	nAdc
Collector Cutoff Current (V_{CE} = −110 Vdc, R_{BE} = 10 kΩ)	I_{CER}	–	–	−10	μAdc
Emitter Cutoff Current (V_{EB} = −6.0 Vdc, I_C = 0)	I_{EBO}	–	–	−200	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = −10 mAdc, V_{CE} = −1.0 Vdc) (I_C = −25 mAdc, V_{CE} = −1.0 Vdc)	h_{FE}	30 30	– –	– –	–
Collector – Emitter Saturation Voltage (I_C = −25 mAdc, I_B = −2.5 mAdc)	$V_{CE(sat)}$	–	–	−250	mVdc
Base – Emitter Saturation Voltage (I_C = −25 mAdc, I_B = −2.5 mAdc)	$V_{BE(sat)}$	–	–	−900	mVdc
SMALL– SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I_C = −25 mAdc, V_{CE} = −5.0 Vdc, f = 20 MHz)	f_T	50	95	–	MHz
Case Capacitance (I_E = I_C = 0, V_{CB} = −10 Vdc, f = 1.0 MHz)	C_C	–	–	20	pF
Noise Figure (I_C = −0.2 mA, V_{CE} = −5.0 Vdc, R_g = 2 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

TYPICAL CHARACTERISTICS

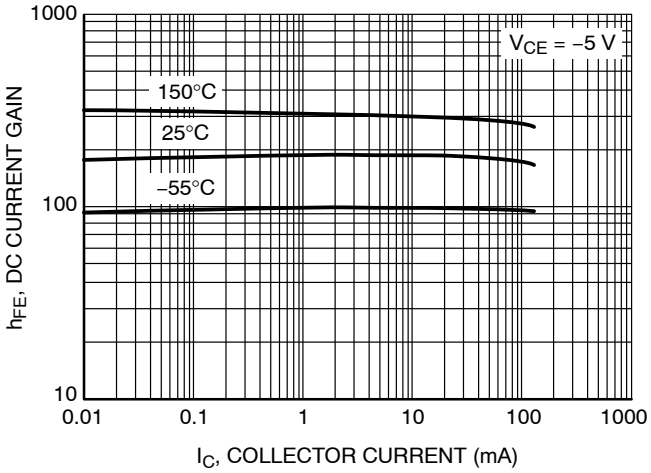


Figure 1. DC Current Gain

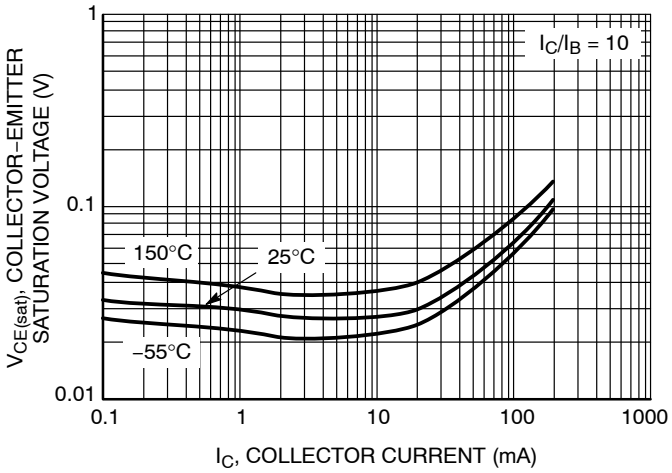


Figure 2. Collector−Emitter Saturation Voltage vs. Collector Current

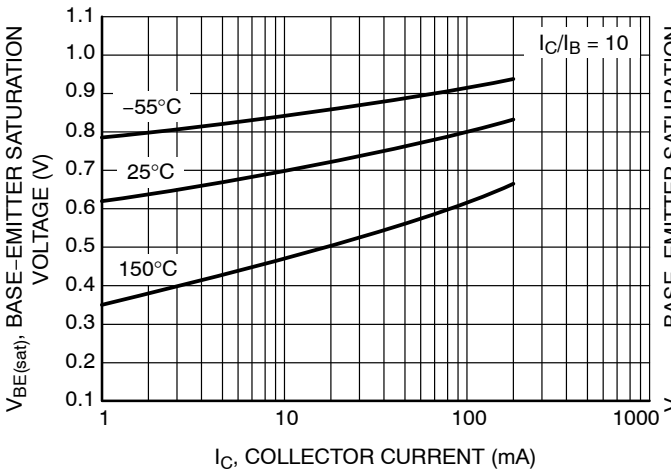


Figure 3. Base−Emitter Saturation Voltage vs. Collector Current

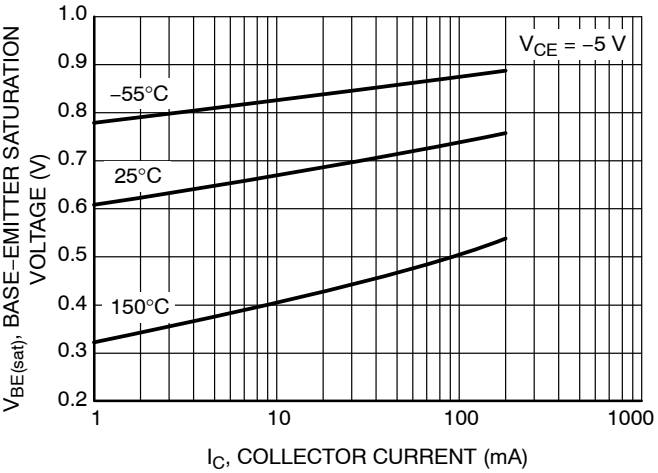


Figure 4. Base−Emitter Voltage vs. Collector Current

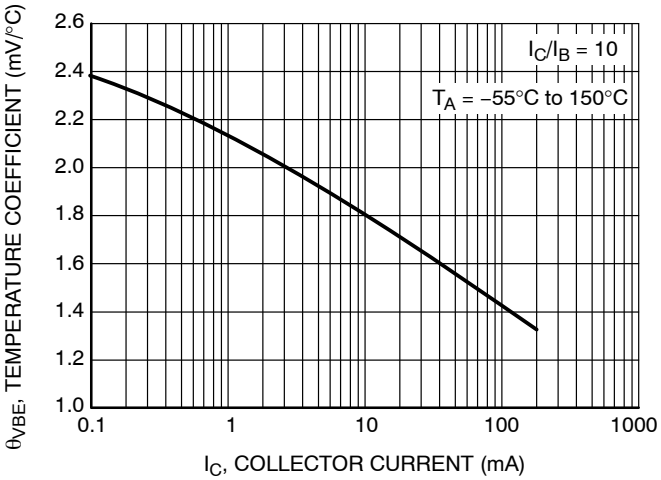


Figure 5. Base−Emitter Temperature Coefficient

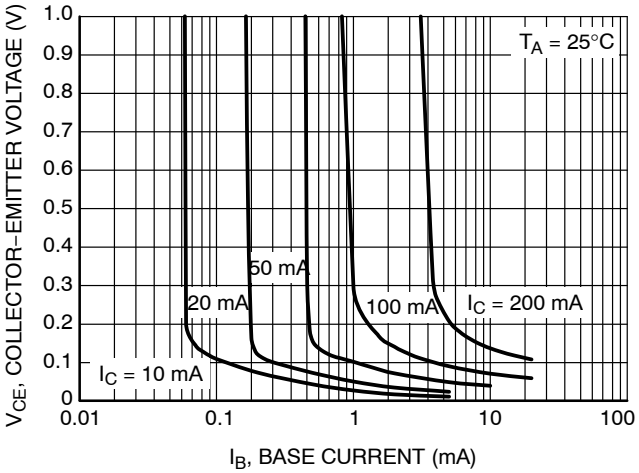


Figure 6. Collector Saturation Region

TYPICAL CHARACTERISTICS

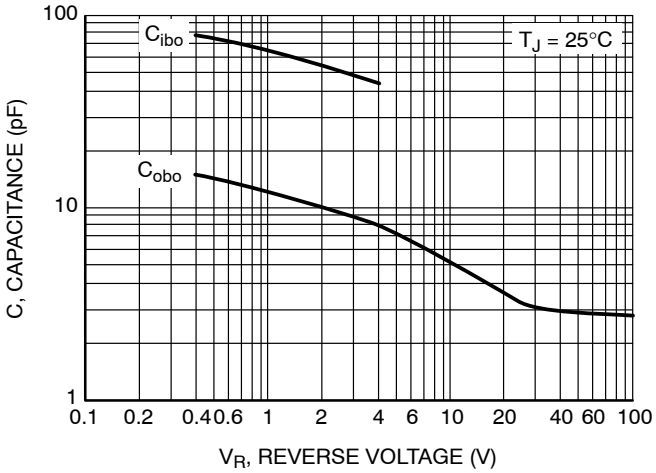


Figure 7. Capacitance

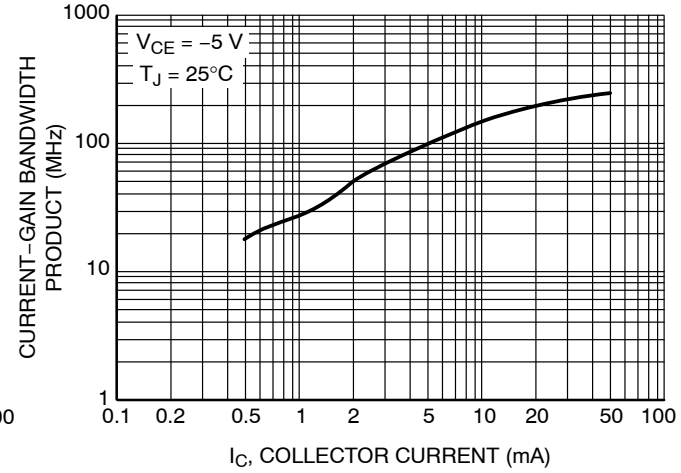


Figure 8. Current−Gain Bandwidth Product

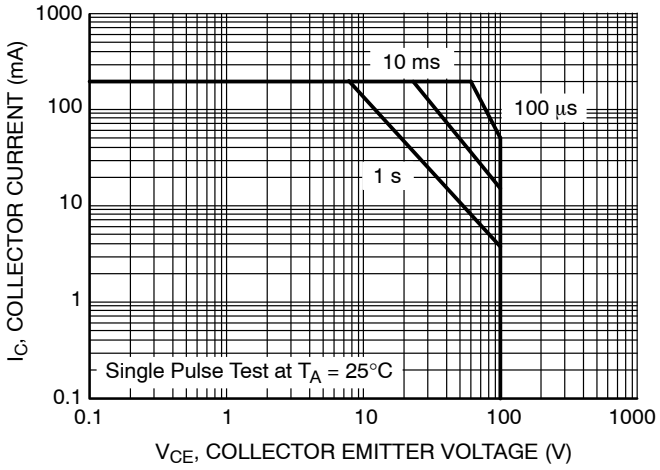
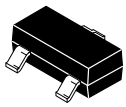


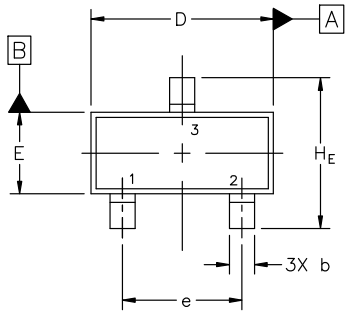
Figure 9. Safe Operating Area



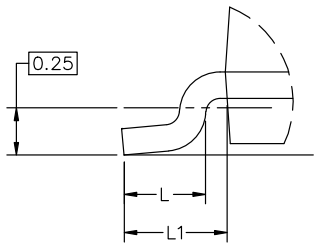
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

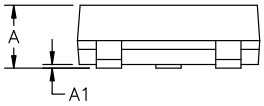
DATE 14 AUG 2024



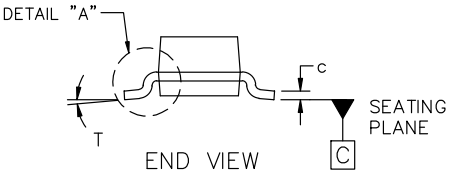
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

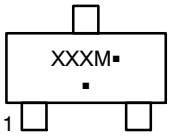


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

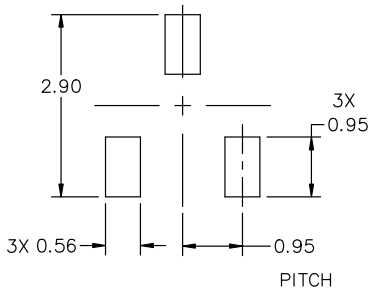
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

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